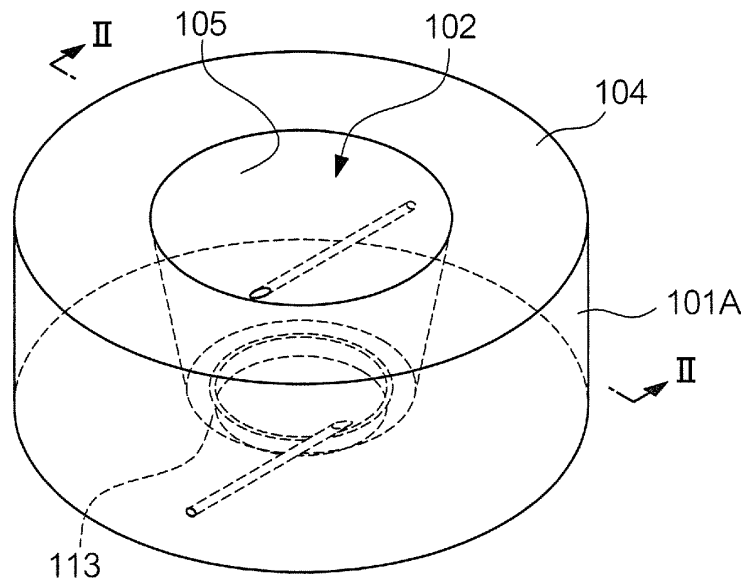


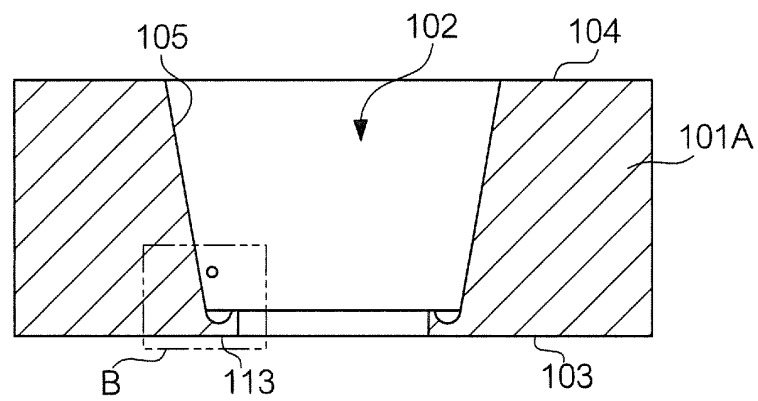


Fig. 10 is a cross-sectional view of a semiconductor device. It shows a substrate 102 with a layer 103, a patterned layer 110, and a layer 1101. A layer 1102 is also shown.

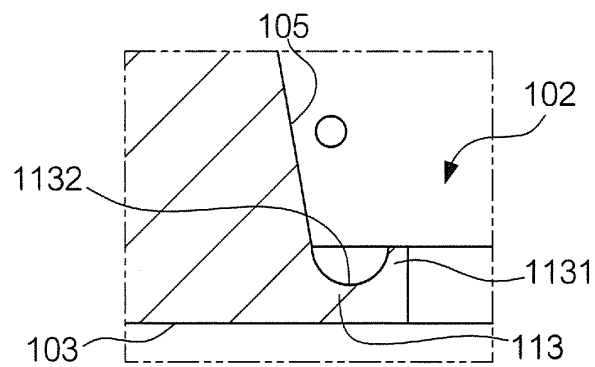
[図5]



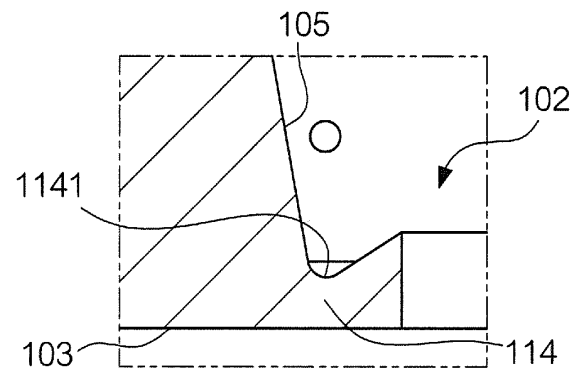
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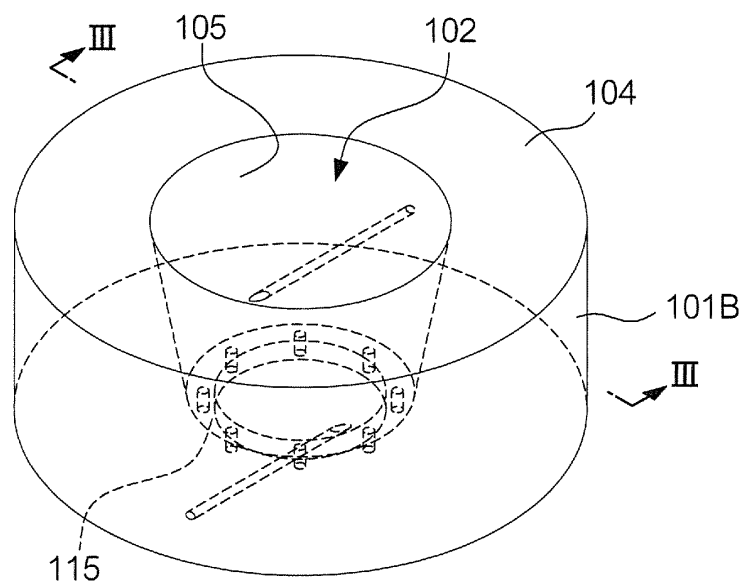
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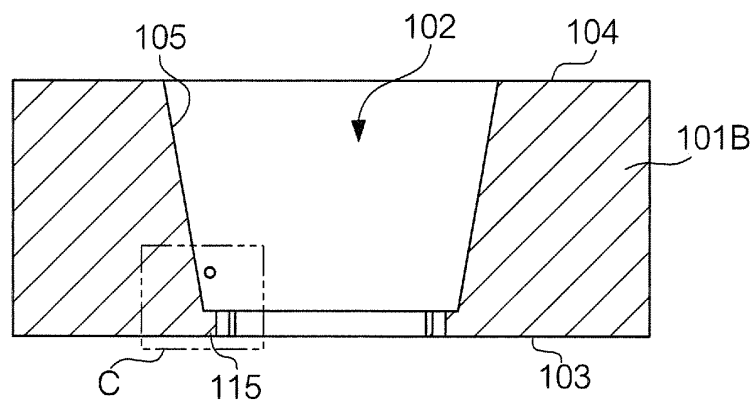
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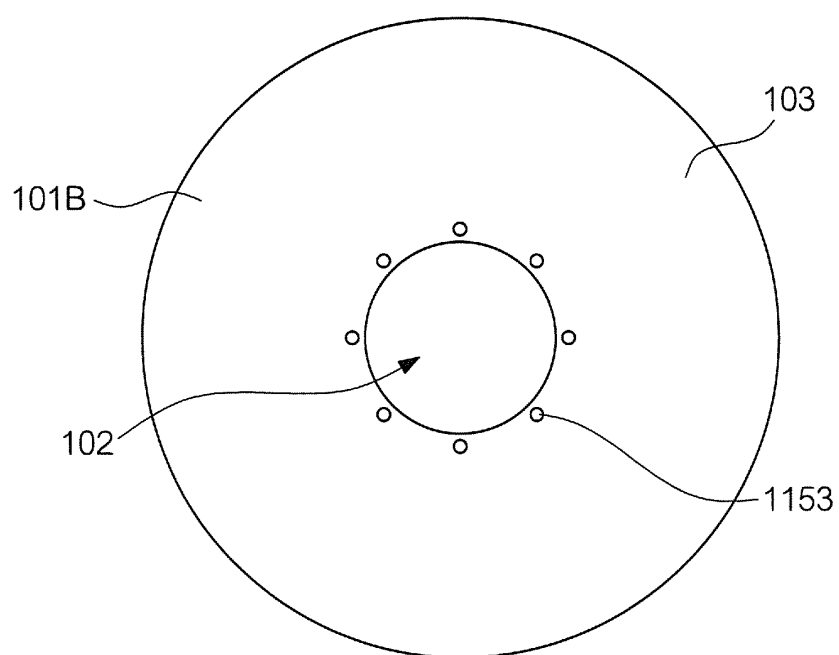
[図9]



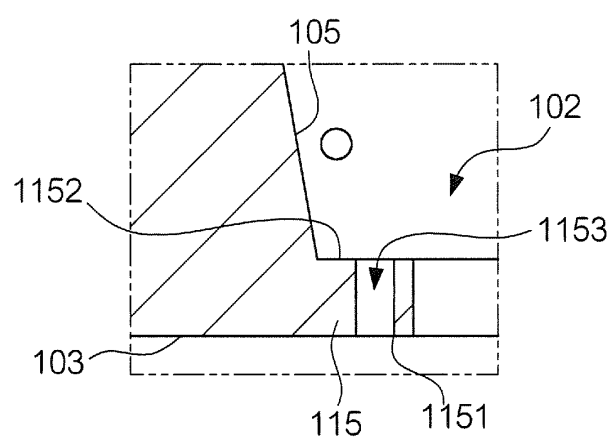
[図10]



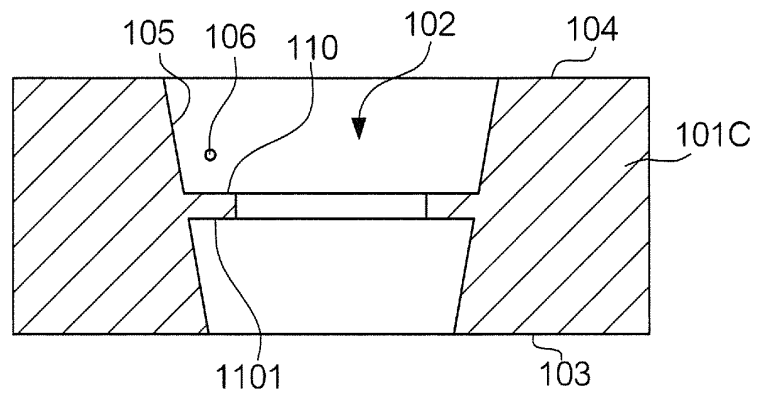
[図11]



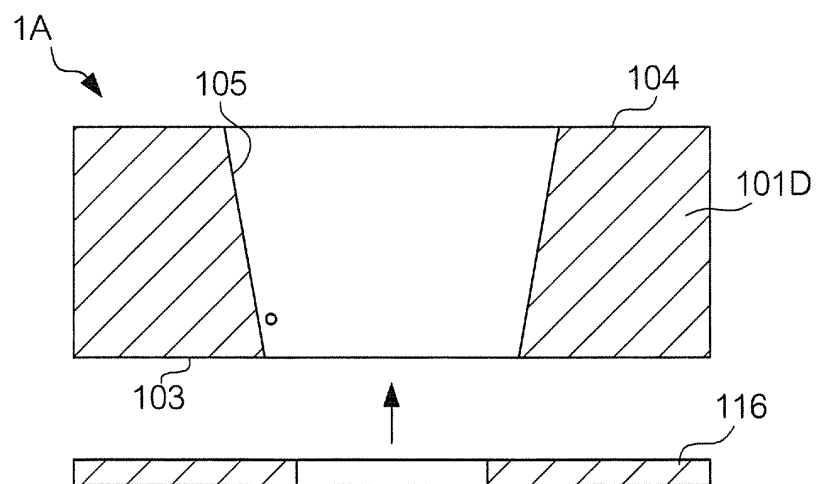
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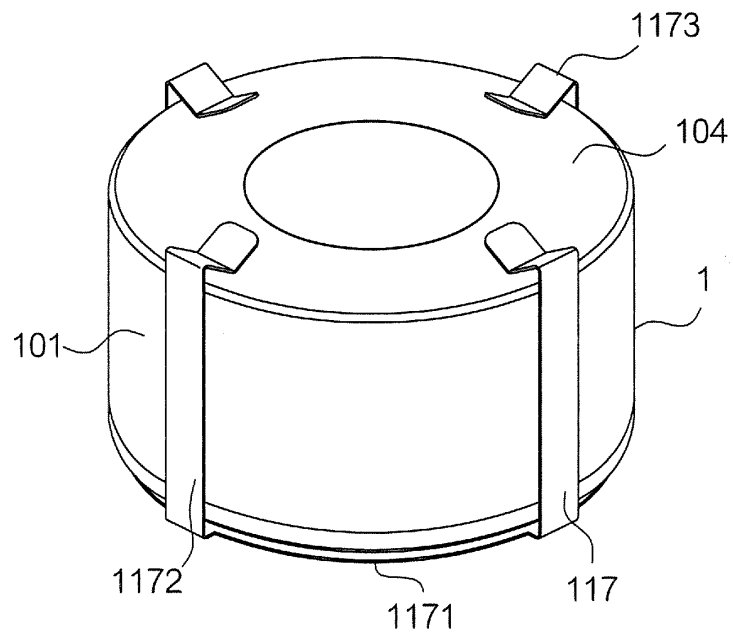
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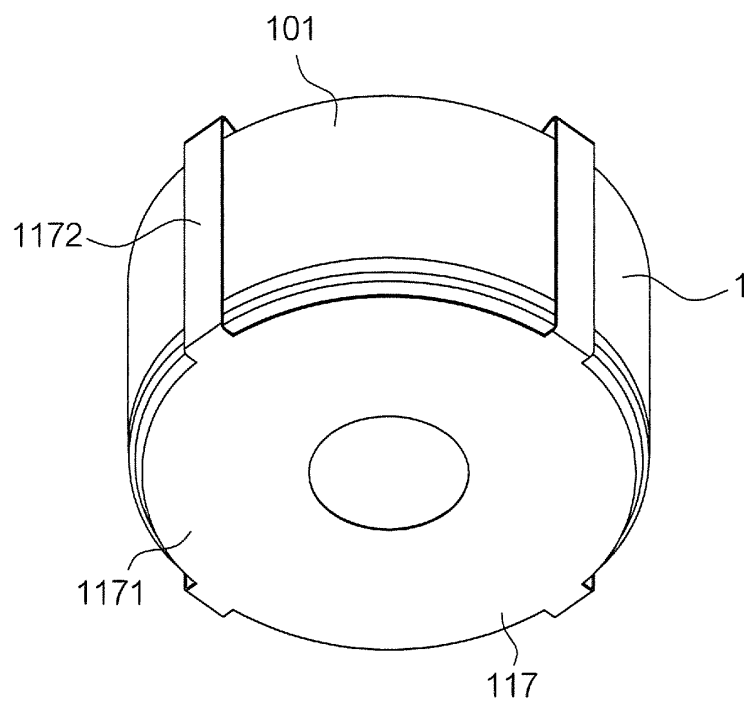
[図14]



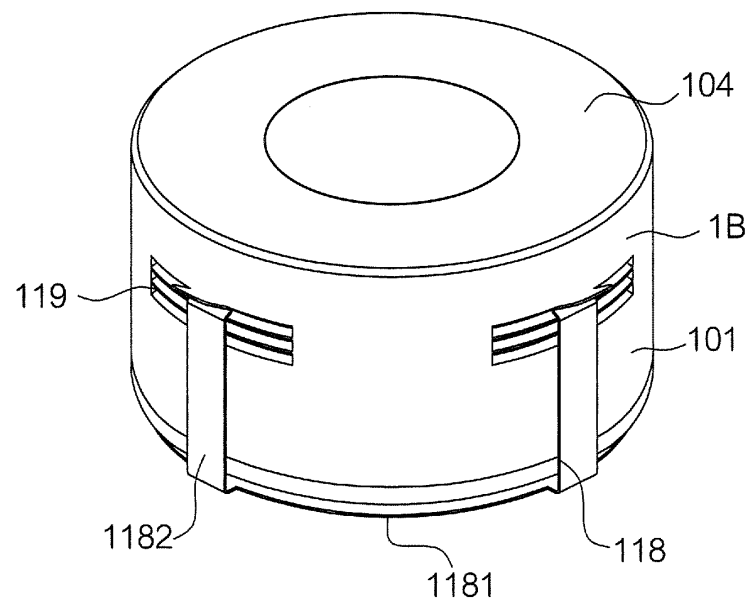
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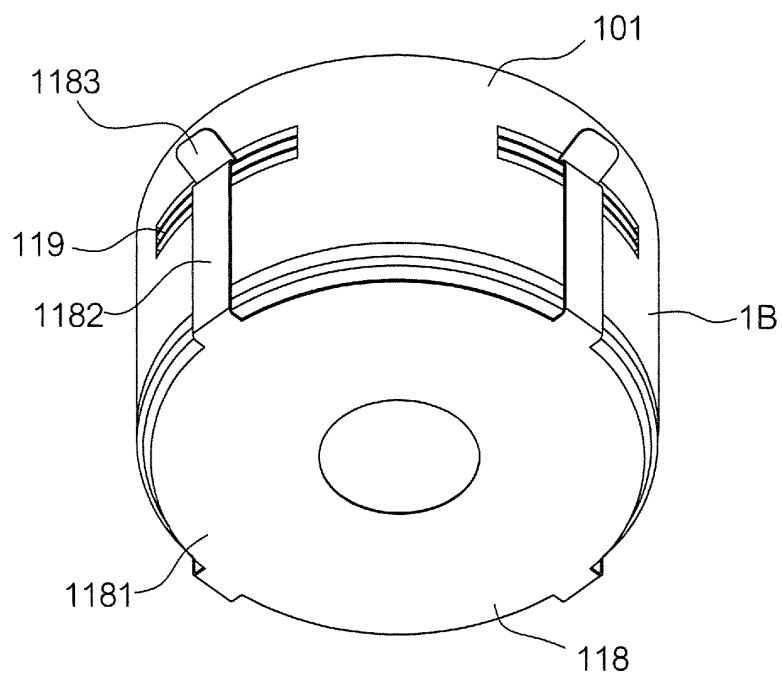
[図16]



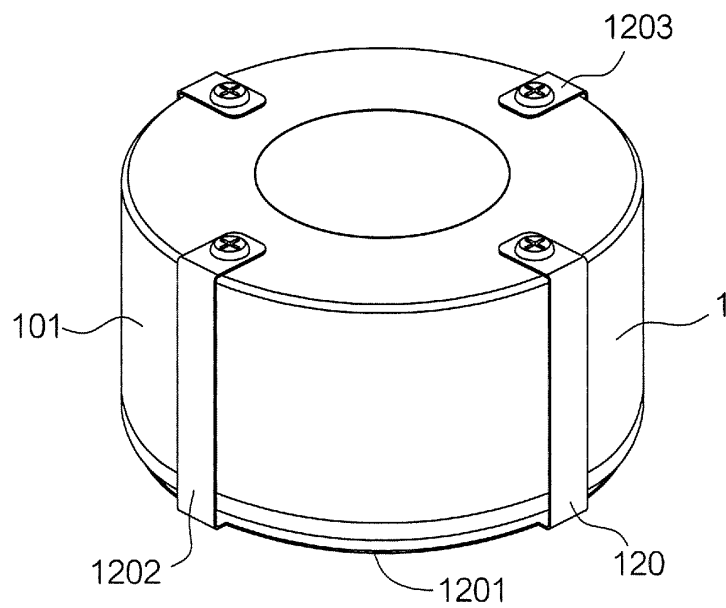
[図17]



[図18]



[図19]



[図20]

